ABSTRACT

Au BONDING WIRE FOR SEMICONDUCTOR DEVICE

Issues to be solved

Au bonding wire for semiconductor device should be provided in circumstances such as reducing the diameter of bonding wire to less than 23 μm, squashed ball with superior roundness should be formed and with strong tensile strength endurable against wire flow.

Means as solution

Au bonding wire for semiconductor device, consisting of Au matrix and functional additives, containing: said Au matrix alloy including 3 - 15 mass ppm of Be, 3 - 40 mass ppm of Ca, and 3 - 20 mass ppm of La and roundness of squashed ball said Au alloy is 0.95 - 1.05.

Figures

Nothing